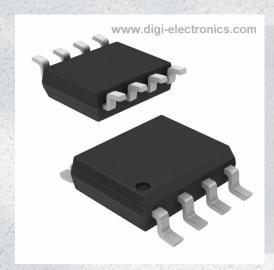


# FDFS2P753Z Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number FDFS2P753Z-DG

Manufacturer onsemi

Manufacturer Product Number FDFS2P753Z

Description MOSFET P-CH 30V 3A 8SOIC

Detailed Description P-Channel 30 V 3A (Ta) 1.6W (Ta) Surface Mount 8-

SOIC



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RFQ Email: Info@DiGi-Electronics.com

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# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
FDFS2P753Z	onsemi
Series:	Product Status:
PowerTrench®	Obsolete
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	3A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
4.5V, 10V	115mOhm @ 3A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
3V @ 250μA	9.3 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±25V	455 pF @ 10 V
FET Feature:	Power Dissipation (Max):
Schottky Diode (Isolated)	1.6W (Ta)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
8-SOIC	8-SOIC (0.154", 3.90mm Width)
Base Product Number:	
FDFS2	

# **Environmental & Export classification**

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



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November 2006

# FDFS2P753Z

# Integrated P-Channel PowerTrench® MOSFET and Schottky Diode

-30V, -3A, 115mΩ

#### **Features**

- Max  $r_{DS(on)}$  = 115m $\Omega$  at  $V_{GS}$  = -10V,  $I_D$  = -3.0A
- Max  $r_{DS(on)}$  = 180m $\Omega$  at  $V_{GS}$  = -4.5V,  $I_D$  = -1.5A
- V<sub>F</sub> < 500mV @ 1A

V<sub>F</sub> < 580mV @ 2A

- Schottky and MOSFET incorporated into single power surface mount SO-8 package
- Electrically independent Schottky and MOSFET pinout for design flexibility
- RoHS Compliant



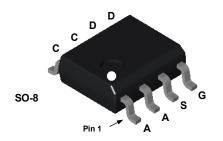
# **General Description**

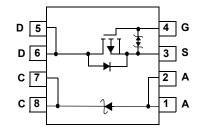
The FDFS2P753Z combines the exceptional performance of Fairchild's PowerTrench MOSFET technology with a very low forward voltage drop Schottky barrier rectifier in an SO-8 package.

This device is designed specifically as a single package solution for DC to DC converters. It features a fast switching, low gate charge MOSFET with very low on-state resistance. The independently connected Schottky diode allows its use in a variety of DC/DC converter topologies.

# **Application**

■ DC - DC Conversion





# **MOSFET Maximum Ratings** $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter		Ratings	Units	
$V_{DS}$	Drain to Source Voltage		-30	V	
$V_{GS}$	Gate to Source Voltage		±25	V	
	Drain Current -Continuous	(Note 1a)	-3	Α	
ID	-Pulsed		-16		
$P_{D}$	Power Dissipation	(Note 1a)	1.6	W	
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 2)		6	mJ	
$V_{RRM}$	Schottky Repetitive Peak Reverse Voltage		-20	V	
Io	Schottky Average Forward Current	(Note 1a)	-2	Α	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C	

#### **Thermal Characteristics**

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	78	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	40	C/VV

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDFS2P753Z	FDFS2P753Z	SO-8	330mm	12mm	2500 units

# **Electrical Characteristics** $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = -250μA, referenced to 25°C		-21		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -24V,$ $V_{GS} = 0V$ $T_{J} = 125^{\circ}C$			-1 -100	μА
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 25V, V_{DS} = 0V$			±10	μА

#### **On Characteristics**

V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-1	-2.1	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, referenced to 25°C		5		mV/°C
	$V_{GS} = -10V, I_D = -3.0A$		69	115		
r	Drain to Source On-Resistance	$V_{GS} = -4.5V$ , $I_{D} = -1.5A$		115	180	mΩ
r <sub>DS(on)</sub> Drain to Sou	Drain to Source On-Resistance	$V_{GS}$ = -10V, $I_{D}$ = -3.0A, $T_{J}$ = 125°C		97	162	11122
g <sub>FS</sub>	Forward Transconductance	$V_{DS} = -5V, I_{D} = -3.0A$		6		S

## **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	\\ - 40\\ \\ - 0\\		340	455	pF
Coss	Output Capacitance	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1MHz		80	110	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - IMHZ		65	100	pF
$R_q$	Gate Resistance	f = 1MHz		18		Ω

## **Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time		7	14	ns
t <sub>r</sub>	Rise Time	$V_{DD} = -10V, I_D = -3.0A$ $V_{GS} = -10V, R_{GEN} = 6\Omega$	31	50	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = -10V, R <sub>GEN</sub> = 052	18	33	ns
t <sub>f</sub>	Fall Time		20	35	ns
$Q_{g(TOT)}$	Total Gate Charge at -10V	V <sub>GS</sub> = 0V to -10V	6.6	9.3	nC
Q <sub>g(4.5)</sub>	Total Gate Charge at -4.5V	$V_{GS} = 0V \text{ to } -4.5V$ $V_{DD} = -10V$ $I_{D} = -3.0A$	3.3	4.6	nC
$Q_{gs}$	Gate to Source Gate Charge	I <sub>D</sub> = -3.0A	1.3		nC
$Q_{gd}$	Gate to Drain "Miller" Charge		1.6		nC

### **Drain-Source Diode Characteristics**

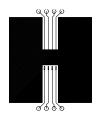
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0V, I_S = -2.0A$ (Note 3)		-0.9	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = -3.0A, di/dt = 100A/μs		20	30	ns
Q <sub>rr</sub>	Reverse Recovery Charge			14	21	nC

## **Schottky Diode Characteristics**

I <sub>R</sub> Reverse Leakage	Payaraa Laakaga	V = 20V	T <sub>J</sub> = 25°C	-190	μΑ
	Reverse Leakage	$V_R = -20V$	T <sub>J</sub> = 125°C	-66	mA
V <sub>F</sub> Forward Voltage		I <sub>E</sub> = 1A	T <sub>J</sub> = 25°C	0.5	
	Forward Voltage	IF - IA	T <sub>J</sub> = 125°C	0.39	V
			T <sub>J</sub> = 25°C	0.58	v
		I <sub>F</sub> = 2A	T <sub>J</sub> = 125°C	0.53	

#### Notes:

 $R_{0JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{0JC}$  is guaranteed by design while  $R_{0CA}$  is determined by the user's board design.



a) 78°C/W when mounted on a 0.5in2 pad of 2 oz copper



b) 135°C/W when mounted on a minimun pad

- 2: Starting T  $_J$  = 25°C, L = 3mH, I  $_{AS}$  = 2A, V  $_{DD}$  = 27V, V  $_{GS}$  = 10V 3: Pulse Test: Pulse Width < 300  $\mu s$ , Duty cycle < 2.0%.

# Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

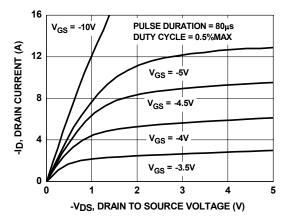


Figure 1. On Region Characteristics

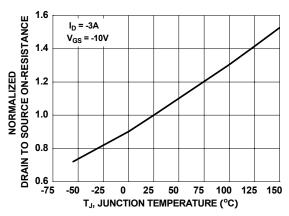


Figure 3. Normalized On-Resistance vs Junction Temperature

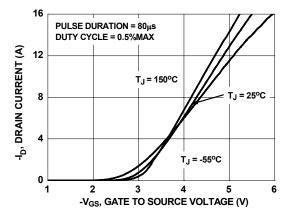


Figure 5. Transfer Characteristics

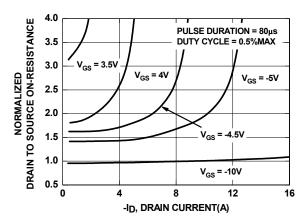


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

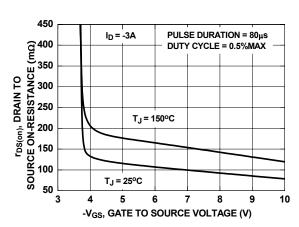


Figure 4. On-Resistance vs Gate to Source Voltage

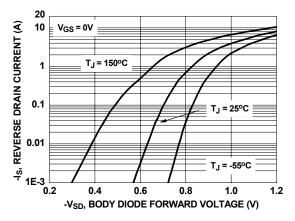


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

## Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

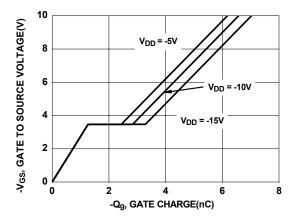


Figure 7. Gate Charge Characteristics

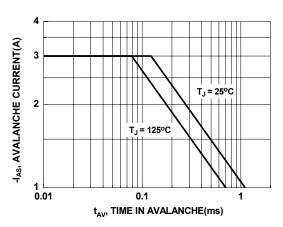


Figure 9. Unclamped Inductive Switching Capability

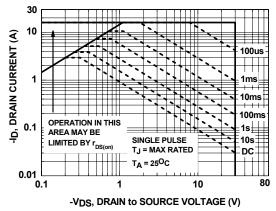


Figure 11. Forward Bias Safe Operating Area

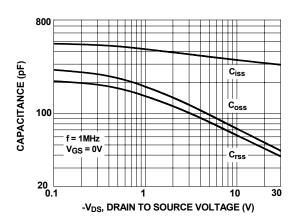


Figure 8. Capacitance vs Drain to Source Voltage

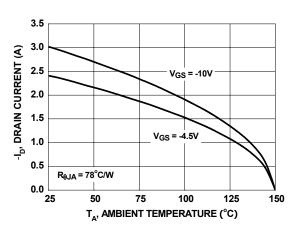


Figure 10. Maximum Continuous Drain Current vs Case Temperature

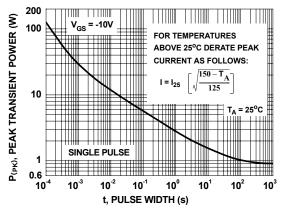
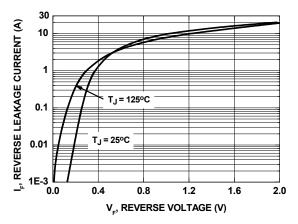


Figure 12. Single Pulse Maximum Power Dissipation

# **Typical Characteristics** T<sub>J</sub> = 25°C unless otherwise noted



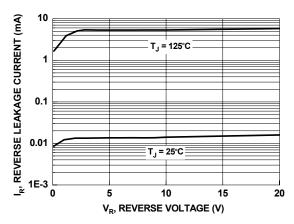


Figure 13. Schottky Diode Forward Voltage

Figure 14. Schottky Diode Reverse Current

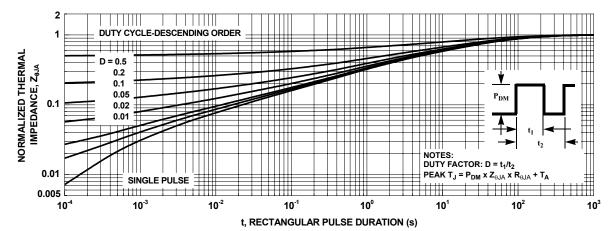


Figure 15. Transient Thermal Response Curve





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